

SEB520S-30
Schottky barrier diode

Revision:A

Features

- Ultra small mold type. (EMD2)
- High reliability.
- Low Ir

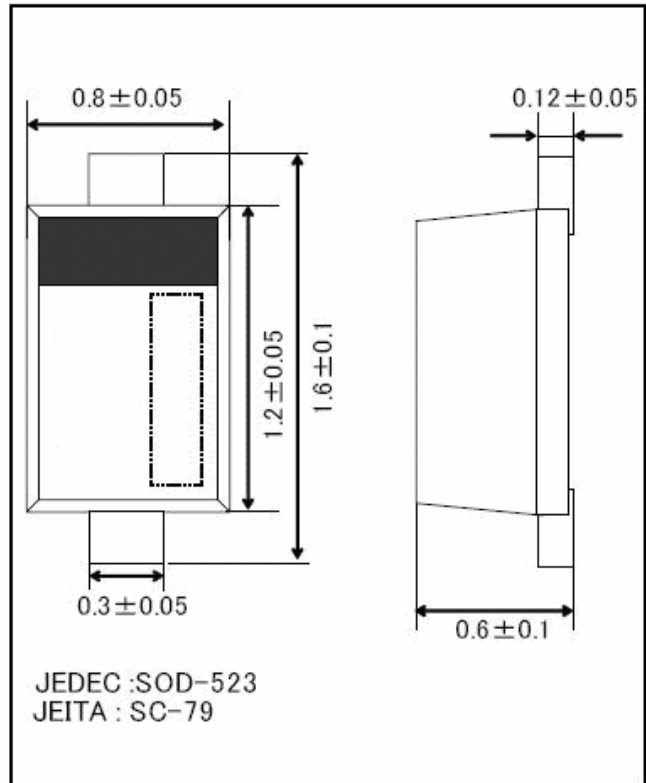
Applications

- Low current rectification

Construction

- Silicon epitaxial planer

External Dimensions



Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
DC reverse voltage	V_R	30	V
Mean rectifying current	I_O	200	mA
Peak forward surge current*	I_{FSM}	1	A
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-40 ~ +125	°C

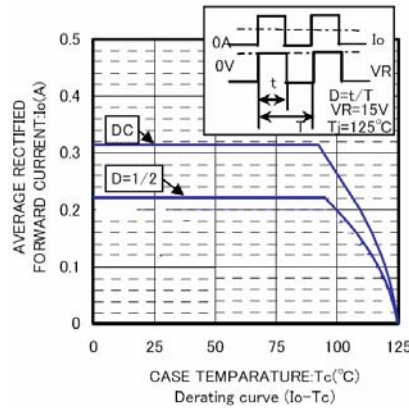
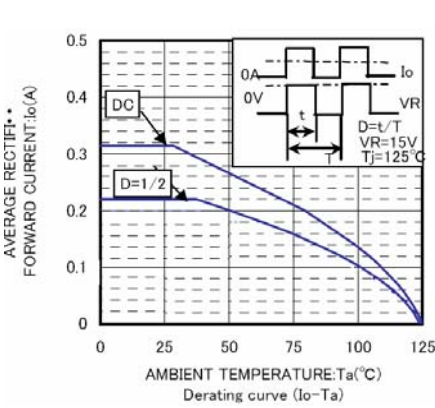
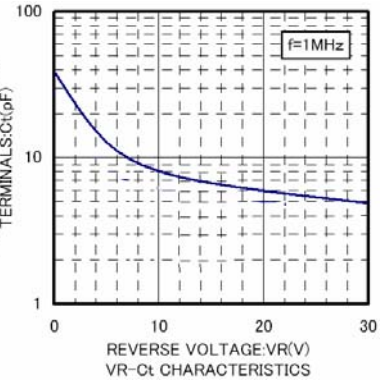
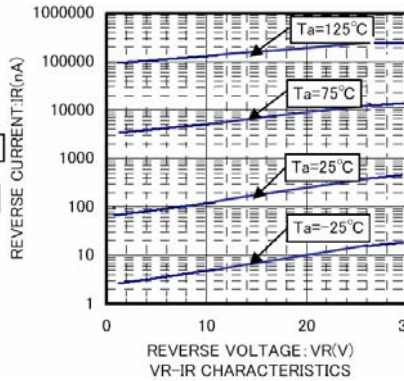
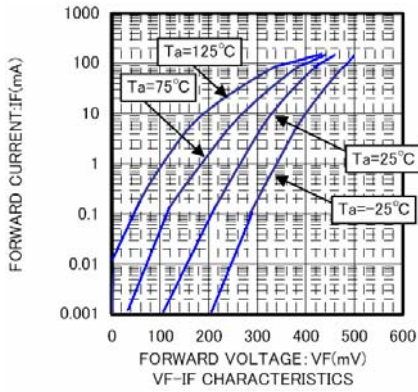
* 60Hz, 1ms

Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	—	—	0.6	V	$I_F = 200\text{mA}$
Reverse current	I_R	—	—	1	uA	$V_R = 10\text{V}$

- Please pay attention to static electricity when handling.

• Electrical characteristic curves (Ta=25°C)



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